



Vincotech

10-EY122PA003MS01-LU39F72T

datasheet

flowDUAL E2 SiC

1200 V / 2,83 mΩ

Topology features

- Gate Resistor
- Half Bridge
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Si₃N₄
- Convex shaped substrate for superior thermal contact
- Compact housing
- CTI600 housing material
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

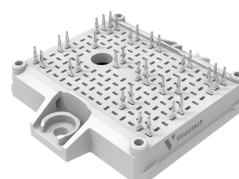
Target applications

- Energy Storage Systems
- General
- Industrial Drives
- Power Supply
- Solar Inverters

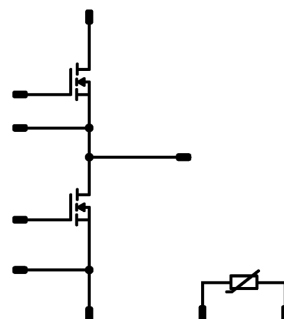
Types

- 10-EY122PA003MS01-LU39F72T

flow E2 12 mm housing



Schematic





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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Inverter Switch				
Drain-source voltage	V_{DS}		1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	368	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	1704	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	554	W
Gate-source voltage	V_{GS}	static	-5 / 18	V
		dynamic	-10 / 22	V
Maximum Junction Temperature	T_{jmax}		175	°C

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Creepage distance			>12,7	mm
Clearance			9,05	mm
Comparative Tracking Index	CTI		≥ 600	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Inverter Switch

Static

Drain-source on-state resistance	$r_{DS(on)}$		18		426	25 125 150		2,89 3,6 3,96	4,17 ⁽¹⁾	mΩ
Gate-source threshold voltage	$V_{GS(th)}$				0,0426	25	1,7	2,25	2,75	V
Gate to Source Leakage Current	I_{GSS}		22	0		25			600	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25			60	μA
Internal gate resistance	r_g							0,167		Ω
Gate charge	Q_g		-5/18	800	426	25		1128		nC
Short-circuit input capacitance	C_{iss}	$f = 500$ kHz	0	800	0	25		28080		pF
Short-circuit output capacitance	C_{oss}							1410		
Reverse transfer capacitance	C_{rss}							48		
Diode forward voltage	V_{SD}		0		426	25		4,1		V

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,17		K/W
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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit				
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max					
Dynamic														
Turn-on delay time	$t_{d(on)}$	$R_{gon} = 1\ \Omega$ $R_{goff} = 1\ \Omega$	-5/18	600	420	25		37,17		ns				
						125		37,51						
						150		36,47						
Rise time	t_r									25		16,8		ns
										125		14,77		
										150		14,63		
Turn-off delay time	$t_{d(off)}$									25		59,91		ns
										125		68,36		
										150		70,28		
Fall time	t_f									25		13,11		ns
										125		13		
										150		13,38		
Turn-on energy (per pulse)	E_{on}	$Q_{rFWD}=3,46\ \mu C$ $Q_{rFWD}=7,66\ \mu C$ $Q_{rFWD}=8,93\ \mu C$				25		3,27		mWs				
						125		3,11						
						150		3,07						
Turn-off energy (per pulse)	E_{off}					25		1,75		mWs				
						125		1,92						
						150		2,01						
Peak recovery current	I_{RRM}	$di/dt=38000\ A/\mu s$ $di/dt=34804\ A/\mu s$ $di/dt=30159\ A/\mu s$				25		280,49		A				
							125		454,49					
							150		501,95					
Reverse recovery time	t_{rr}						25		20,22		ns			
							125		26,41					
							150		28					
Recovered charge	Q_r						25		3,46		μC			
							125		7,66					
							150		8,93					
Reverse recovered energy	E_{rec}						25		1,15		mWs			
							125		2,89					
							150		3,4					
Peak rate of fall of recovery current	$(di_{rr}/dt)_{max}$					25		51685,61		A/ μs				
						125		95220,59						
						150		119141,29						



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		5		kΩ
Deviation of R100	$\Delta_{R/R}$	$R_{100} = 499 \Omega$				100	3,2		3,3	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,3		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 1 \%$						3380		K
Vincotech Thermistor Reference									V	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.

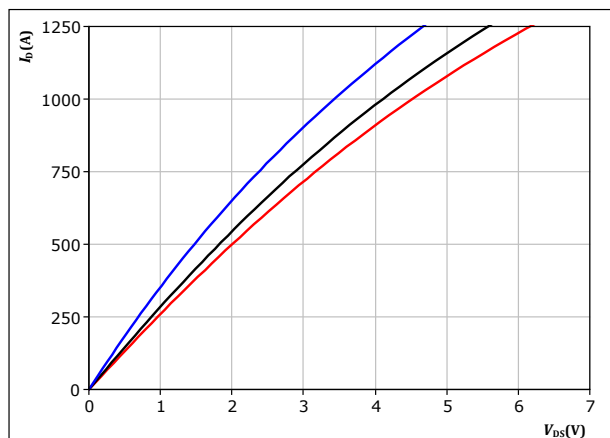


Inverter Switch Characteristics

figure 1. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$



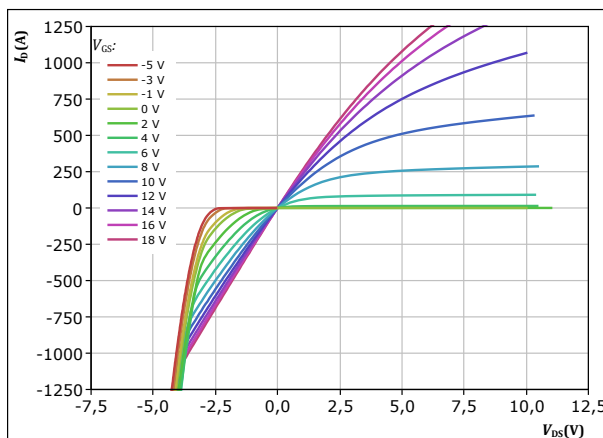
$t_p = 250 \mu s$
 $V_{GS} = 18 V$

$T_j:$
— 25 °C
— 125 °C
— 150 °C

figure 2. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

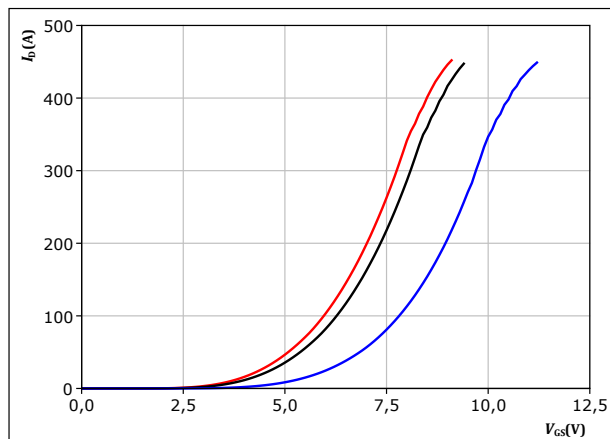


$t_p = 250 \mu s$
 $T_j = 150 ^\circ C$
 V_{GS} from -5 V to 18 V in steps of 2 V

figure 3. MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$



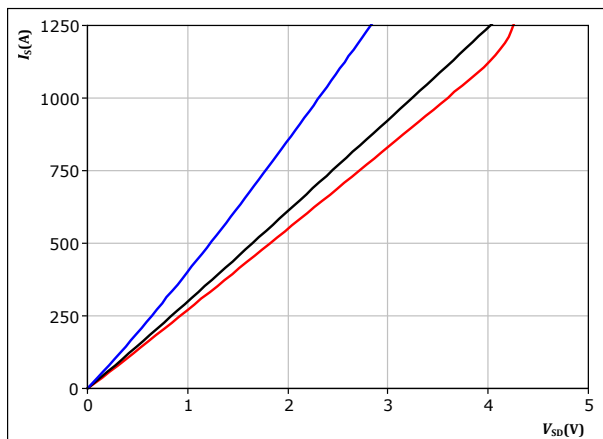
$t_p = 250 \mu s$
 $V_{DS} = 27 V$

$T_j:$
— 25 °C
— 125 °C
— 150 °C

figure 4. MOSFET

Typical reverse drain current characteristics

$$I_{SD} = f(V_{SD})$$



$t_p = 250 \mu s$
 $V_{GS} = 18 V$

$T_j:$
— 25 °C
— 125 °C
— 150 °C



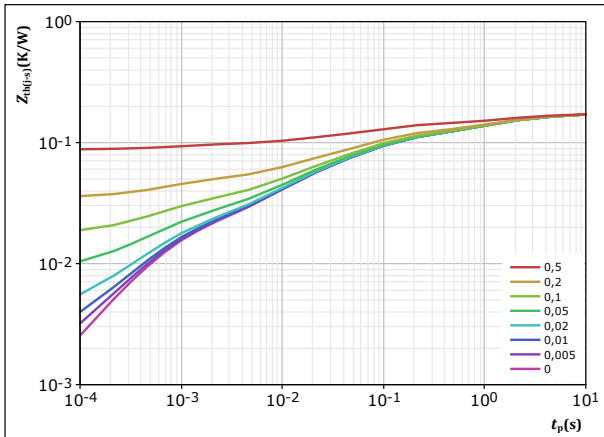
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Inverter Switch Characteristics

figure 5. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$$D = t_p / T$$

$$R_{th(j-s)} = 0,171 \text{ K/W}$$

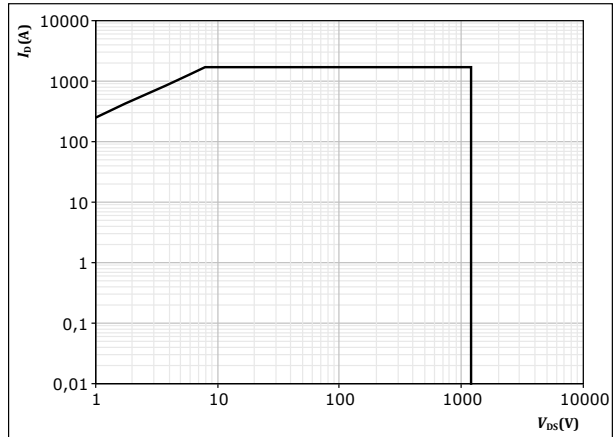
MOSFET thermal model values

R (K/W)	τ (s)
2,33E-02	5,74E+00
4,76E-02	9,86E-01
5,95E-02	7,19E-02
2,88E-02	1,11E-02
1,57E-02	6,63E-04

figure 6. MOSFET

Safe operating area

$$I_D = f(V_{DS})$$



$D = \text{single pulse}$

$$T_s = 80 \text{ } ^\circ\text{C}$$

$$V_{GS} = 18 \text{ V}$$

$$T_j = T_{jmax}$$



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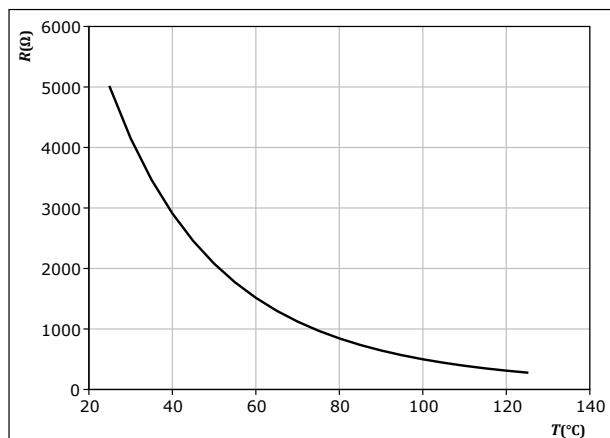
Thermistor Characteristics

figure 7.

Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$





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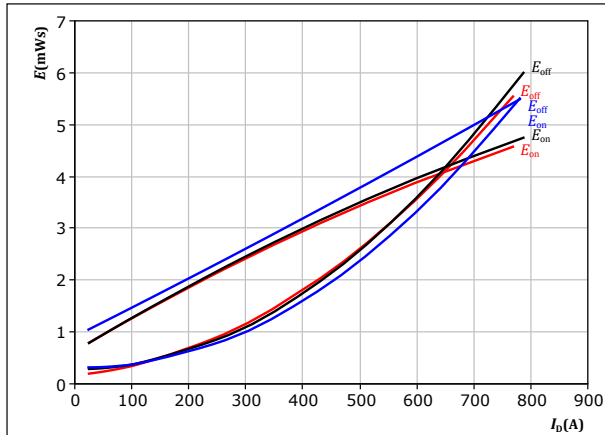
Inverter Switching Characteristics

figure 8.

MOSFET

Typical switching energy losses as a function of drain current

$$E = f(I_D)$$



With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $R_{gon} = 1$ Ω
 $R_{goff} = 1$ Ω

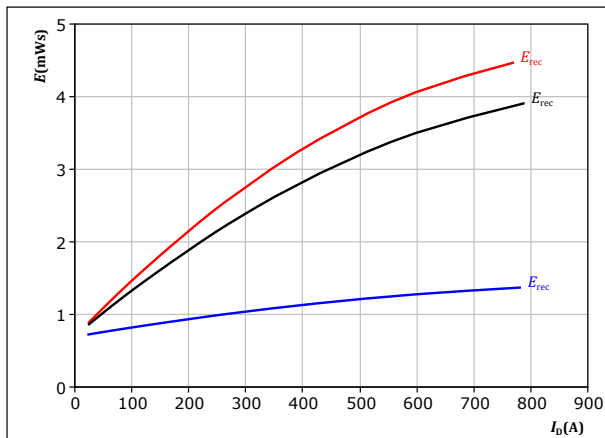
T_j : 25 °C
125 °C
150 °C

figure 10.

MOSFET

Typical reverse recovered energy loss as a function of drain current

$$E_{rec} = f(I_D)$$



With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $R_{gon} = 1$ Ω

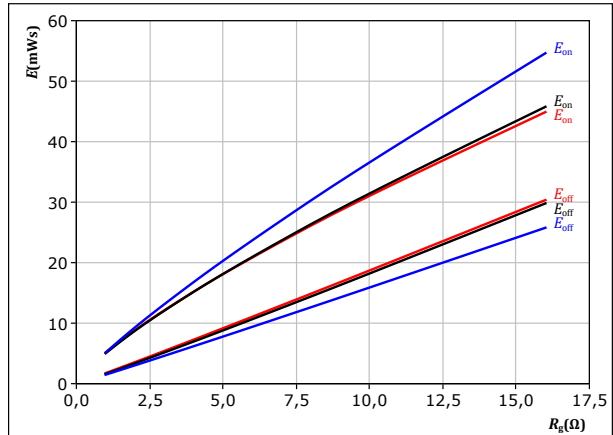
T_j : 25 °C
125 °C
150 °C

figure 9.

MOSFET

Typical switching energy losses as a function of MOSFET turn on gate resistor

$$E = f(R_g)$$



With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $I_D = 420$ A

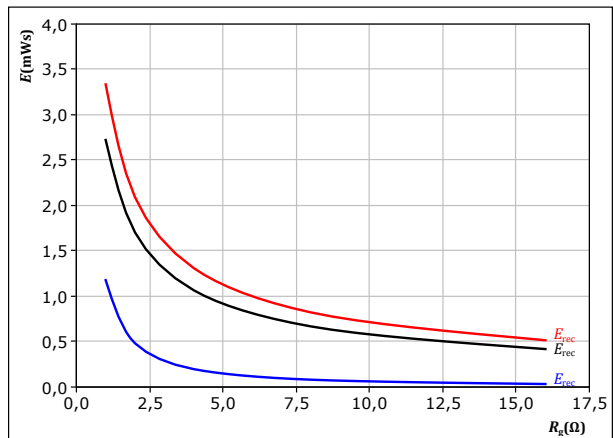
T_j : 25 °C
125 °C
150 °C

figure 11.

MOSFET

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $I_D = 420$ A

T_j : 25 °C
125 °C
150 °C



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Inverter Switching Characteristics

figure 12. MOSFET

Typical switching times as a function of drain current
 $t = f(I_D)$

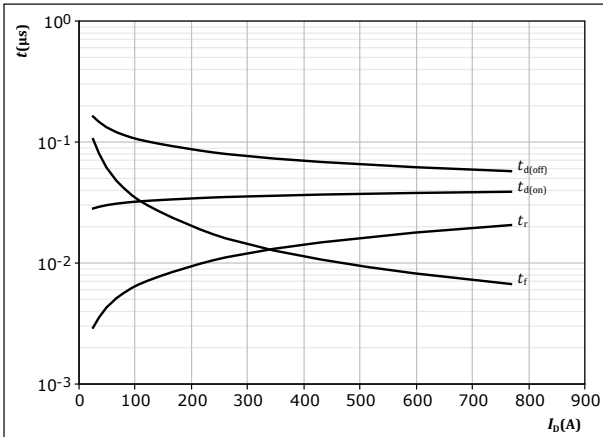


figure 13. MOSFET

Typical switching times as a function of MOSFET turn on gate resistor
 $t = f(R_g)$

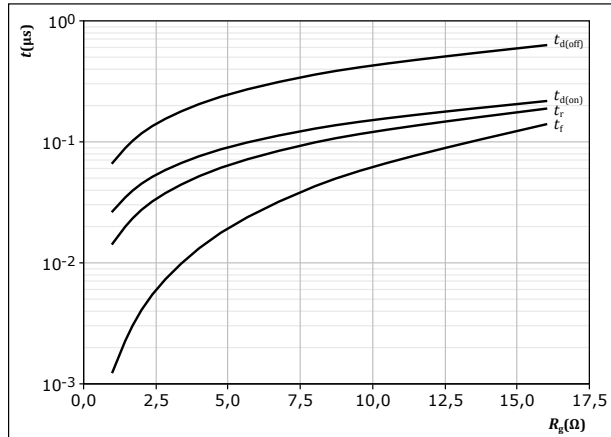


figure 14. MOSFET

Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$

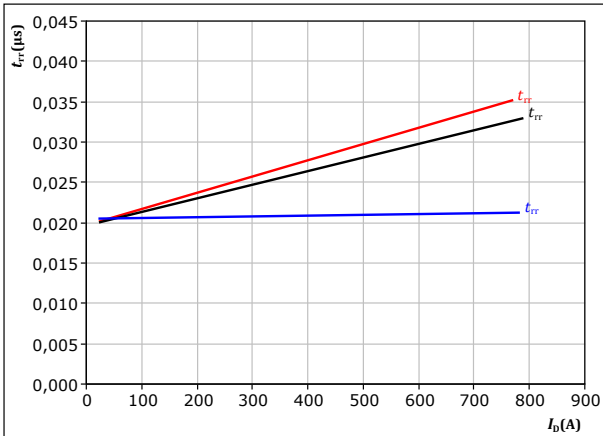
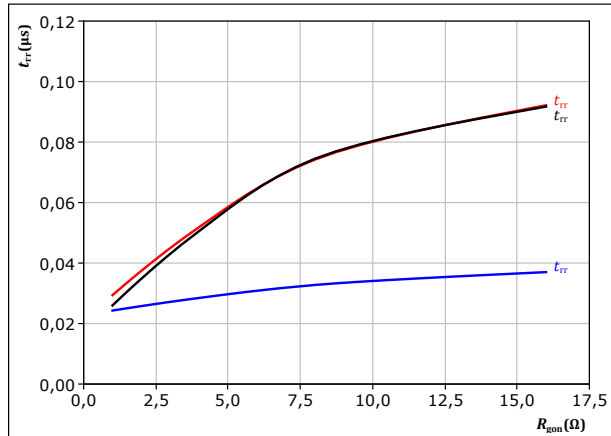


figure 15. MOSFET

Typical reverse recovery time as a function of MOSFET turn on gate resistor
 $t_{rr} = f(R_{gon})$





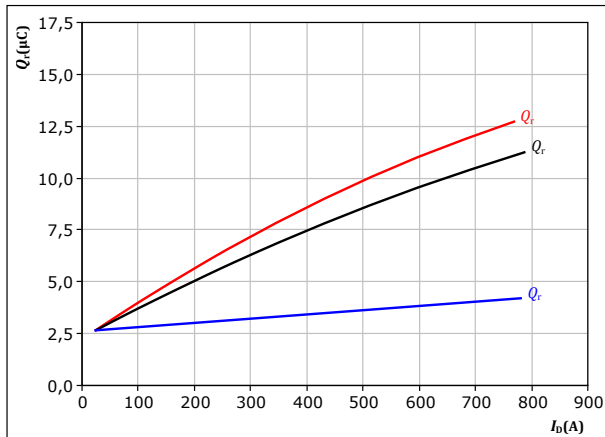
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Inverter Switching Characteristics

figure 16. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$

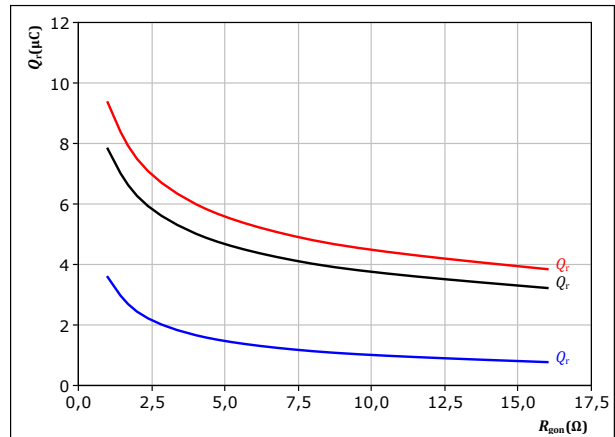


At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $R_{gon} = 1$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 17. MOSFET

Typical recovered charge as a function of MOSFET turn on gate resistor

$$Q_r = f(R_{gon})$$

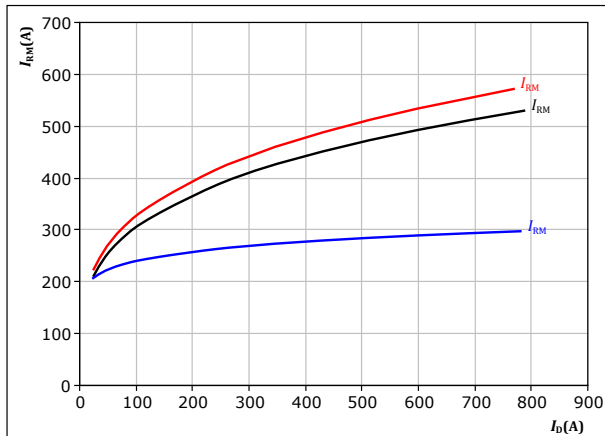


At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $I_D = 420$ A
 T_j : 25 °C
125 °C
150 °C

figure 18. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$

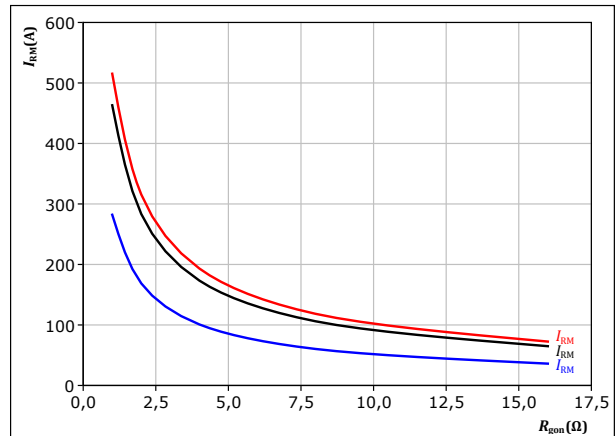


At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $R_{gon} = 1$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 19. MOSFET

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $I_D = 420$ A
 T_j : 25 °C
125 °C
150 °C



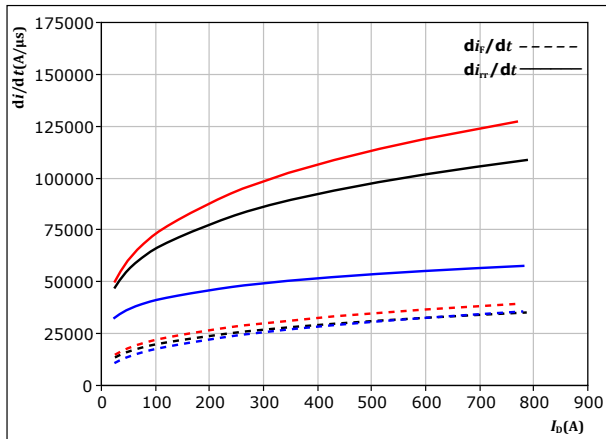
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Inverter Switching Characteristics

figure 20. MOSFET

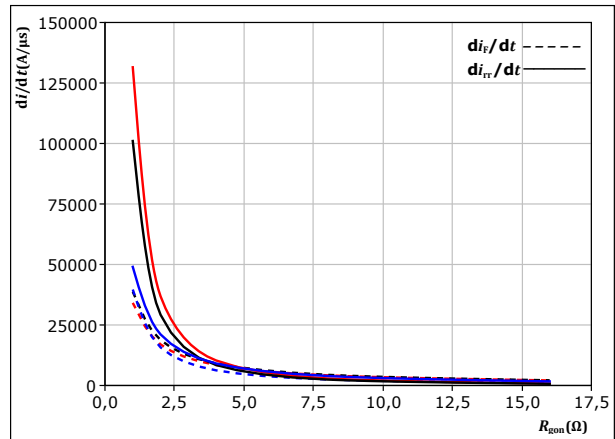
Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_r/dt = f(I_D)$



At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $R_{gon} = 1$ Ω
 $T_j: 25$ °C
125 °C
150 °C

figure 21. MOSFET

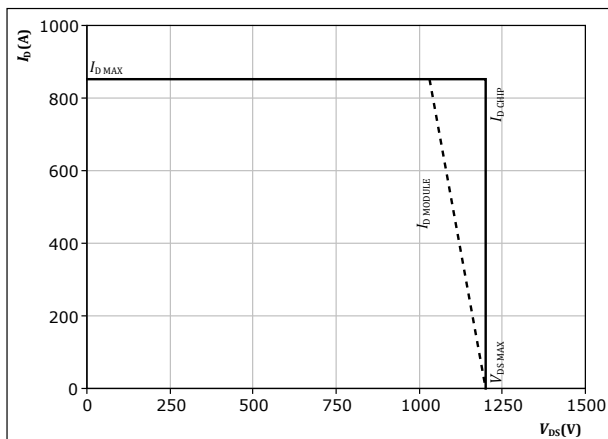
Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



At $V_{DS} = 600$ V
 $V_{GS} = -5/18$ V
 $I_D = 420$ A
 $T_j: 25$ °C
125 °C
150 °C

figure 22. MOSFET

Reverse bias safe operating area
 $I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{gon} = 1$ Ω
 $R_{goff} = 1$ Ω



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Inverter Switching Definitions

figure 23. MOSFET

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

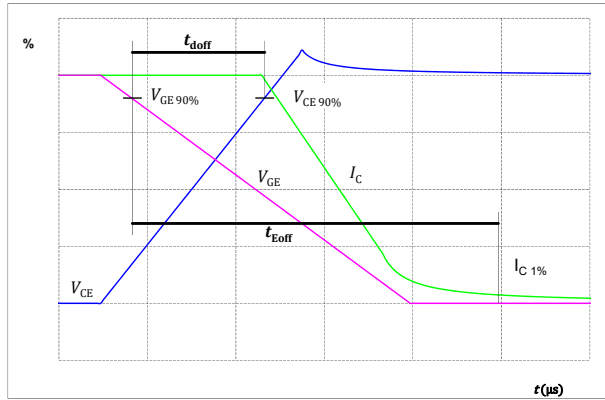


figure 24. MOSFET

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

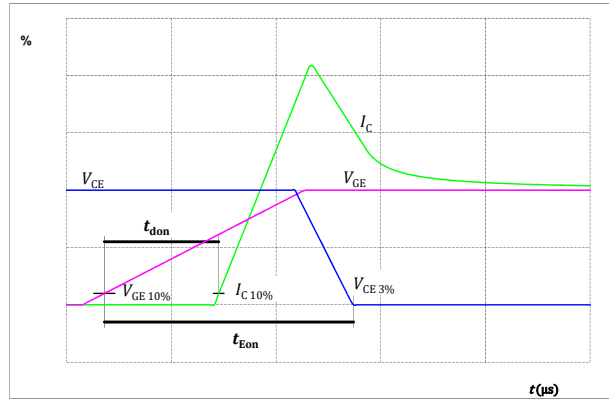


figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_f

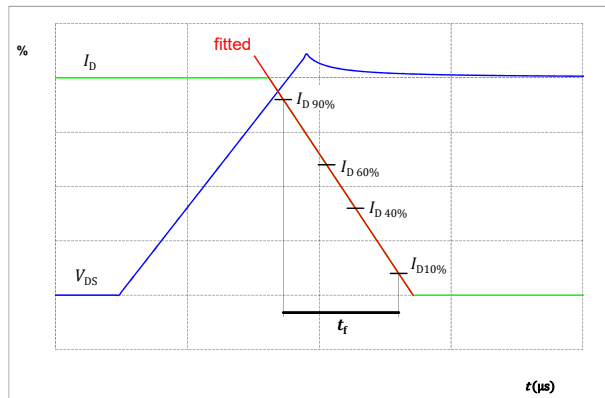
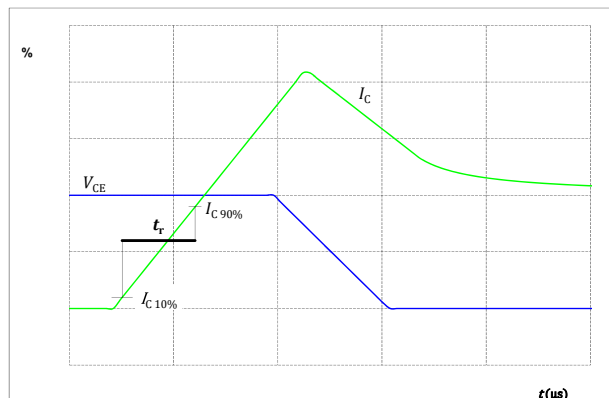


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_r





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Inverter Switching Definitions

figure 27. FWD

Turn-off Switching Waveforms & definition of t_{tr}

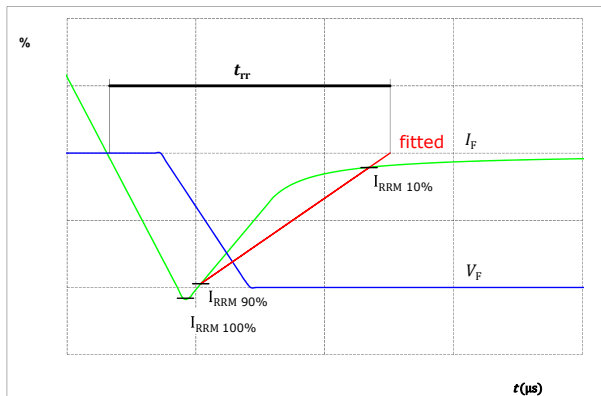


figure 28. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

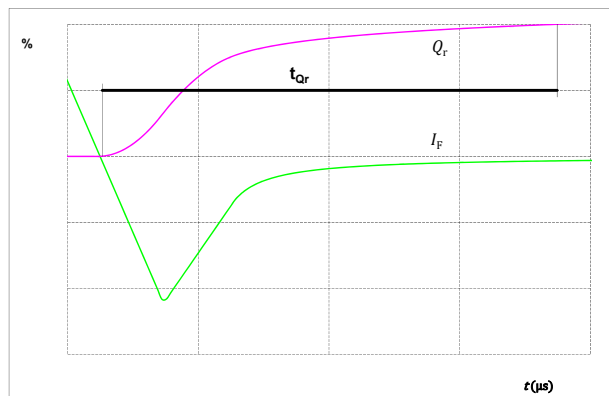
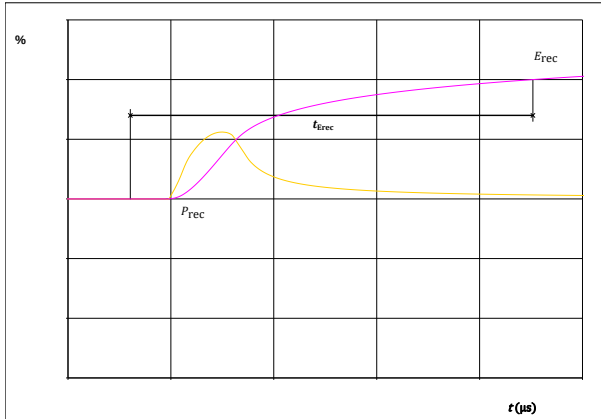


figure 29. FWD

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})





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datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-EY122PA003MS01-LU39F72T
With thermal paste (5,2 W/mK, PTM6000HV)	10-EY122PA003MS01-LU39F72T-/7/

Marking							
 NLN000000000000000 TTTTTIVVWY UL VIN LLLLL SSSS	Text	Name		Date code	UL & VIN	Lot	Serial
		NN-NNNNNNNNNNNNN- TTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTIVV	LLLLL	SSSS	WWYY			

Pin table [mm]

Pin	X	Y	Function
1	25,6	48	Ph1
2	28,8	48	Ph1
3	32	48	Ph1
4	28,8	44,8	Ph1
5	32	44,8	Ph1
6	28,8	35,2	S11
7	32	35,2	G11
8	32	28,8	Therm1
9	32	25,6	Therm2
10	28,8	12,8	S11
11	32	12,8	G11
12	28,8	3,2	Ph1
13	32	3,2	Ph1
14	32	0	Ph1
15	28,8	0	Ph1
16	25,6	0	Ph1
17	19,2	6,4	DC-
18	16	9,6	DC-
19	16	16	DC-
20	16	19,2	DC-
21	19,2	19,2	DC-
22	16	28,8	DC-
23	19,2	28,8	DC-
24	19,2	41,6	DC-
25	12,8	48	DC+
26	9,6	48	DC+
27	6,4	35,2	DC+
28	3,2	35,2	DC+
29	6,4	12,8	DC+
30	3,2	12,8	DC+
31	12,8	0	DC+
32	9,6	0	DC+
33	0	0	S12
34	0	3,2	G12
35	0	44,8	G12
36	0	48	S12

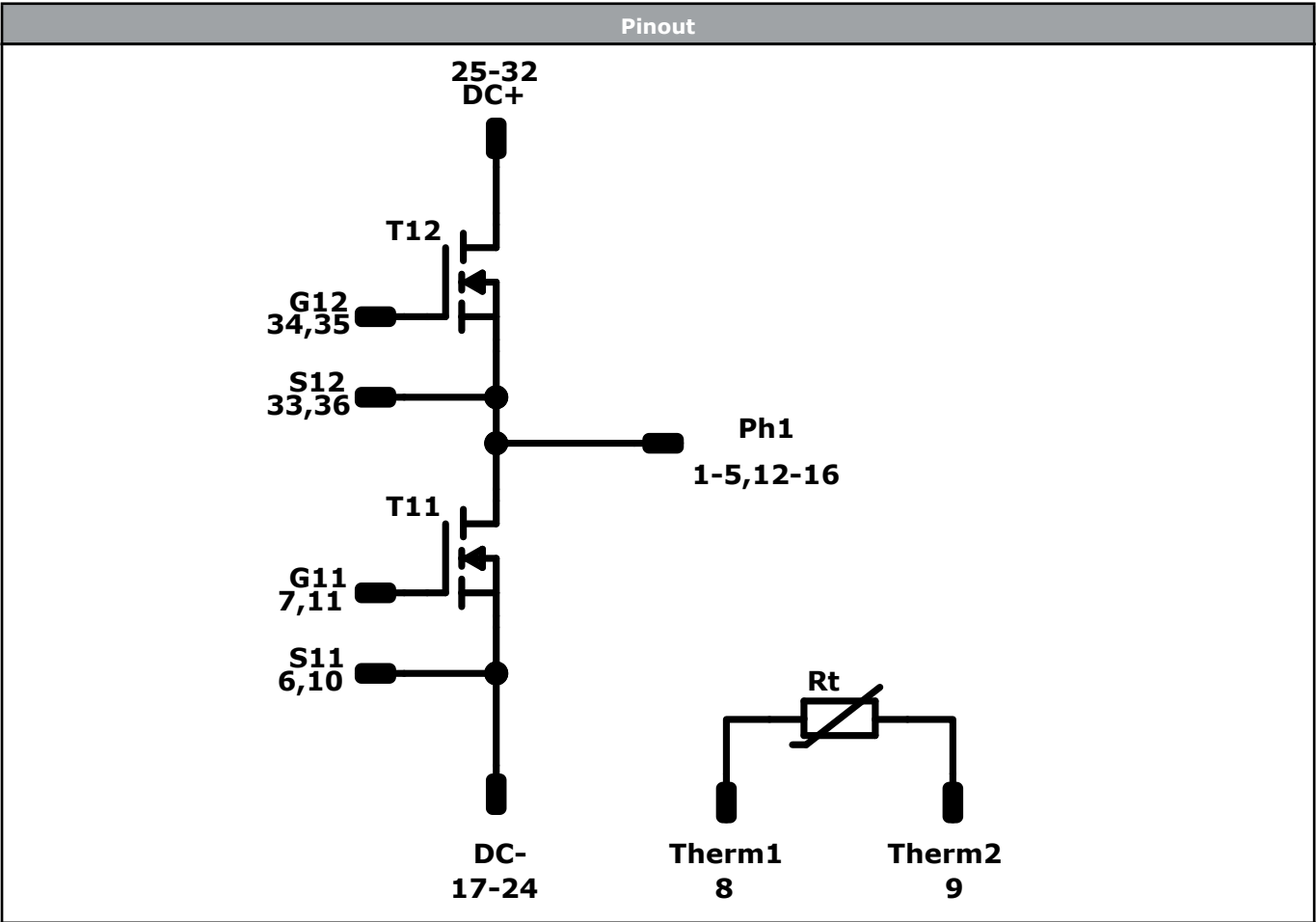
Outline

The technical drawing shows the sensor module from two perspectives. The top view is a square layout with a central circular feature and a grid of pins. The side view shows the module's profile with a height of 9,68 ± 0,1 mm and a width of 34,1 ± 0,5 mm. A note specifies: 'center of press-fit pin head pin head type "P" PDS placed through-hole Ø1mm ±0,09 / ±0,06 for further PDS design rules refer to the latest handling instruction'.

Tolerance of positions: ±0,4mm at the end of pins
 Dimension of coordinate axis is only offset without tolerance



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Identification					
ID	Component	Voltage	Current	Function	Comment
T11, T12	MOSFET	1200 V	2,83 mΩ	Inverter Switch	
Rt	Thermistor			Thermistor	



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datasheet

Packaging instruction				
Standard packaging quantity (SPQ) 100	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow</i> E2 packages see vincotech.com website.

Package data
Package data for <i>flow</i> E2 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is UL 1557 recognized under E192116 up to a junction temperature under switching condition $T_{j,op}=175^{\circ}\text{C}$ and up to 3500VAC/1min isolation voltage. For more information see vincotech.com website.



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.